

## NCE N-Channel Super Trench II Power MOSFET

### Description

The NCEP065N10GU uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

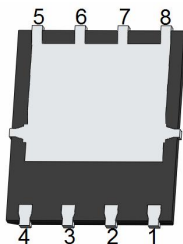
- $V_{DS} = 100V, I_D = 90A$   
 $R_{DS(ON)} = 5.9m\Omega$  (typical) @  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

**100% UIS TESTED!**  
**100%  $\Delta V_{ds}$  TESTED!**

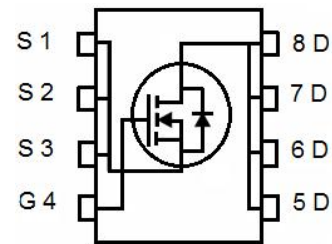
### DFN 5X6



Top View



Bottom View



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P065N10GU	NCEP065N10GU	DFN5X6-8L	-	-	-

### Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	90	A
Drain Current-Continuous( $T_c = 100^\circ C$ )	$I_D(100^\circ C)$	65	A
Pulsed Drain Current	$I_{DM}$	360	A
Maximum Power Dissipation	$P_D$	110	W
Derating factor		0.88	W/ $^\circ C$
Single pulse avalanche energy (Note 1)	$E_{AS}$	380	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.14	$^{\circ}C/W$
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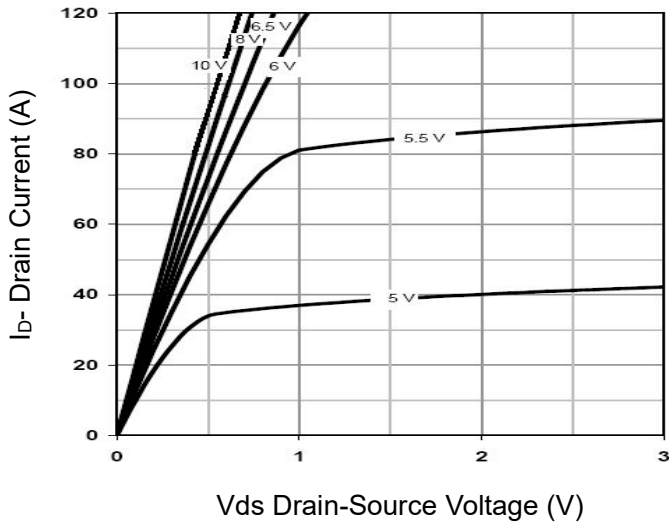
## Electrical Characteristics ( $T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=45A$	-	5.9	6.5	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=45A$		60	-	S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$	-	3600	-	PF
Output Capacitance	$C_{oss}$		-	335	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	19.5	-	PF
<b>Switching Characteristics</b> (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=45A,$ $V_{GS}=10V, R_G=3\Omega$	-	17	-	nS
Turn-on Rise Time	$t_r$		-	11	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	36	-	nS
Turn-Off Fall Time	$t_f$		-	9	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=50V, I_D=45A,$ $V_{GS}=10V$	-	60	-	nC
Gate-Source Charge	$Q_{gs}$		-	20		nC
Gate-Drain Charge	$Q_{gd}$		-	15		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=45A$	-		1.2	V
Diode Forward Current	$I_S$		-	-	90	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}C, I_F = 45A$	-	62	-	nS
Reverse Recovery Charge	$Q_{rr}$	$di/dt = 100A/\mu s$	-	109	-	nC

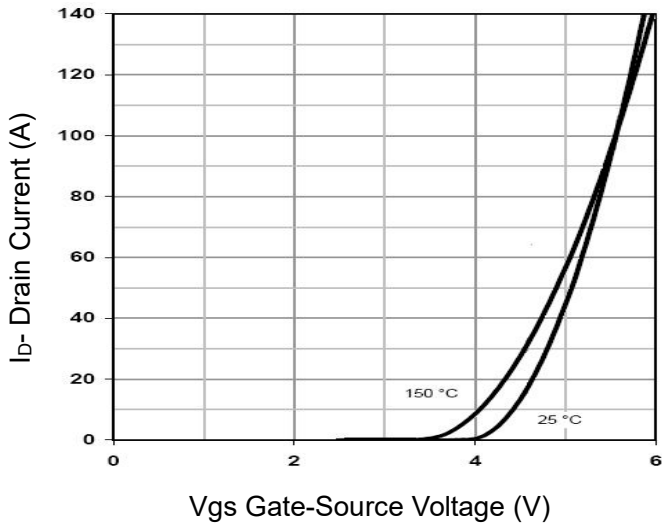
### Notes:

1. EAS condition :  $T_J=25^{\circ}C, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of  $T_J(MAX)=150^{\circ}C$ . The SOA curve provides a single pulse rating.

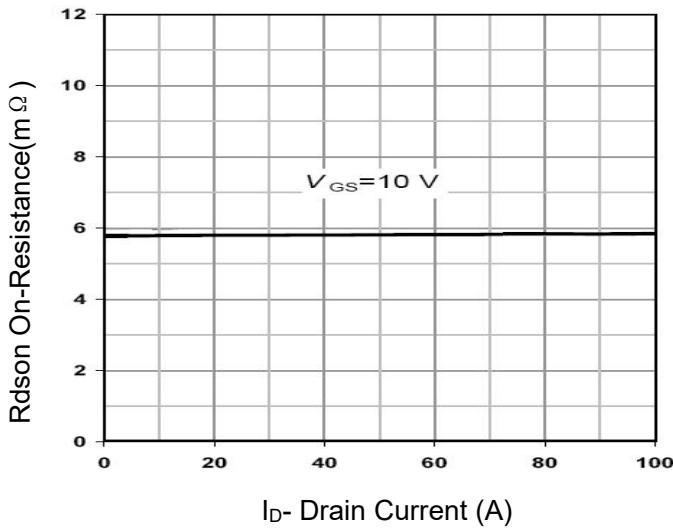
## Typical Electrical and Thermal Characteristics



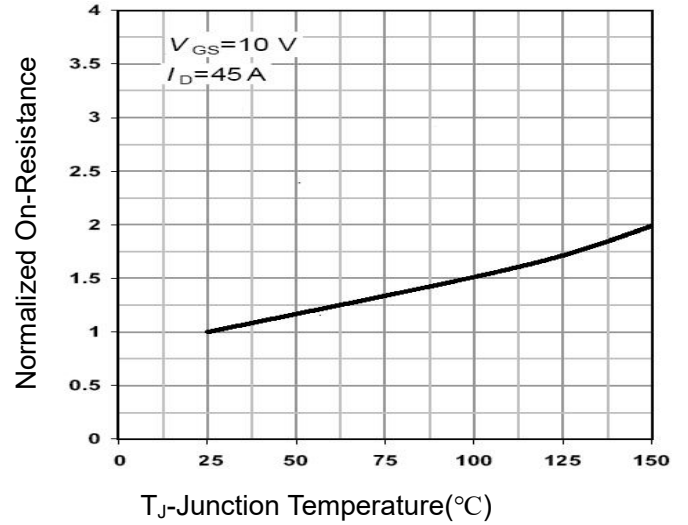
**Figure 1 Output Characteristics**



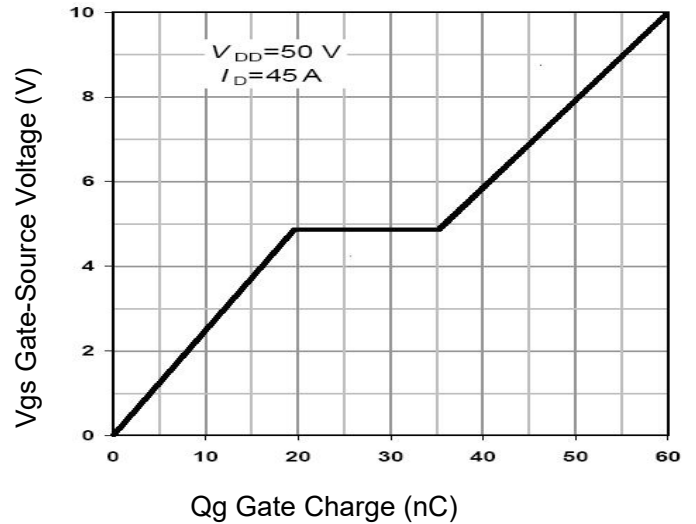
**Figure 2 Transfer Characteristics**



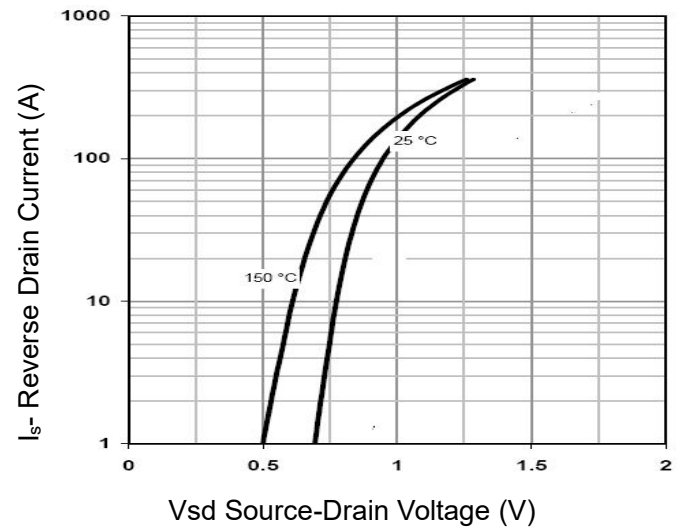
**Figure 3 Rdson- Drain Current**



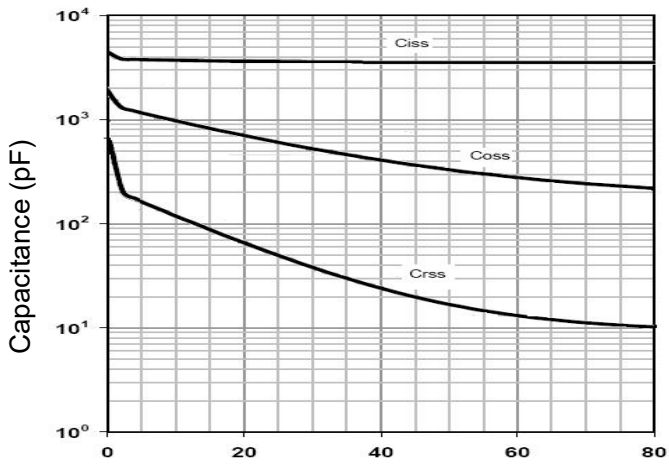
**Figure 4 Rdson-Junction Temperature**



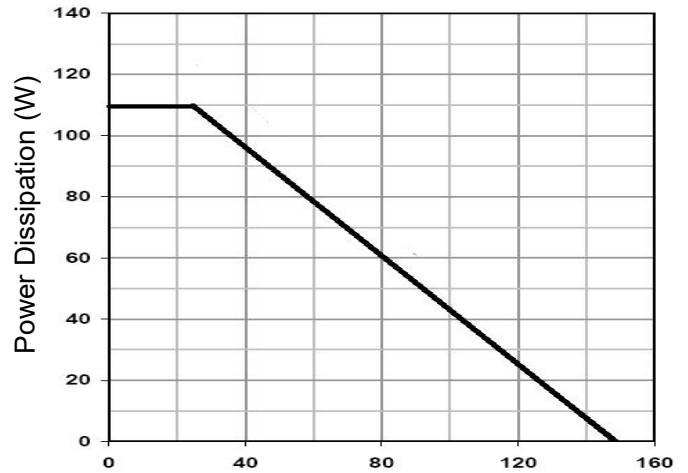
**Figure 5 Gate Charge**



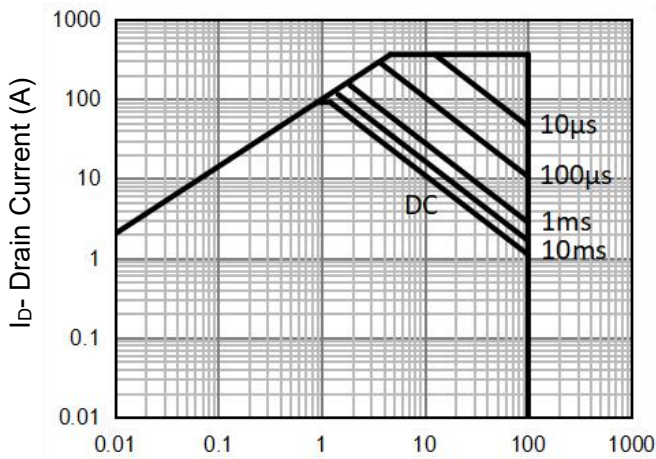
**Figure 6 Source- Drain Diode Forward**



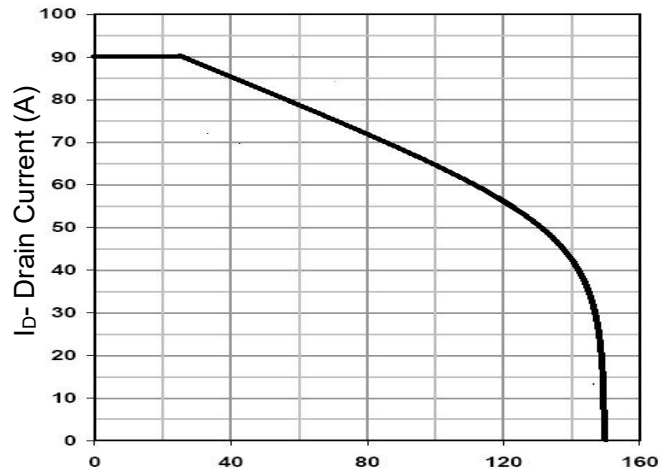
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



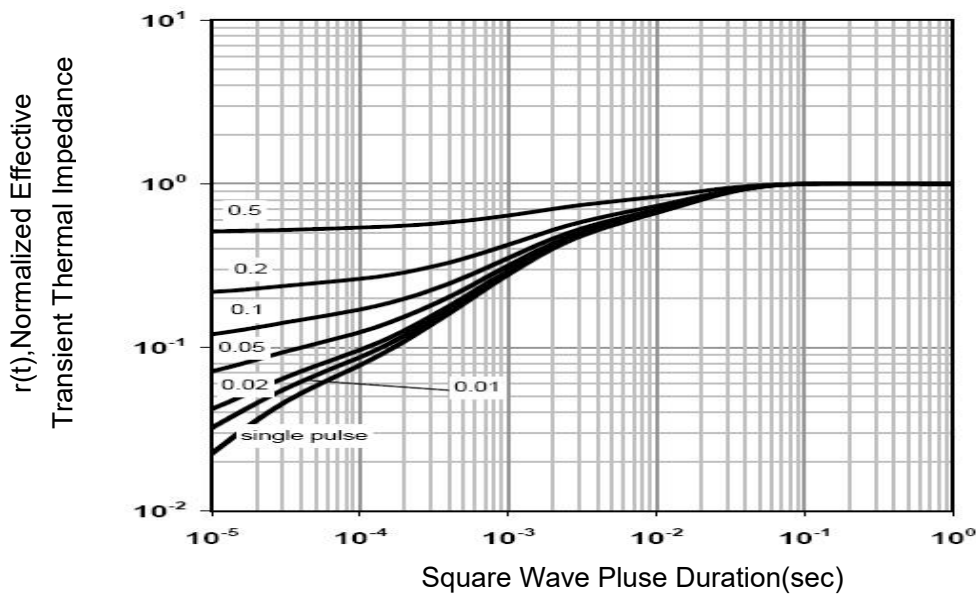
TA-Junction Temperature(°C)  
**Figure 9 Power De-rating**



Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area** (Note 3)

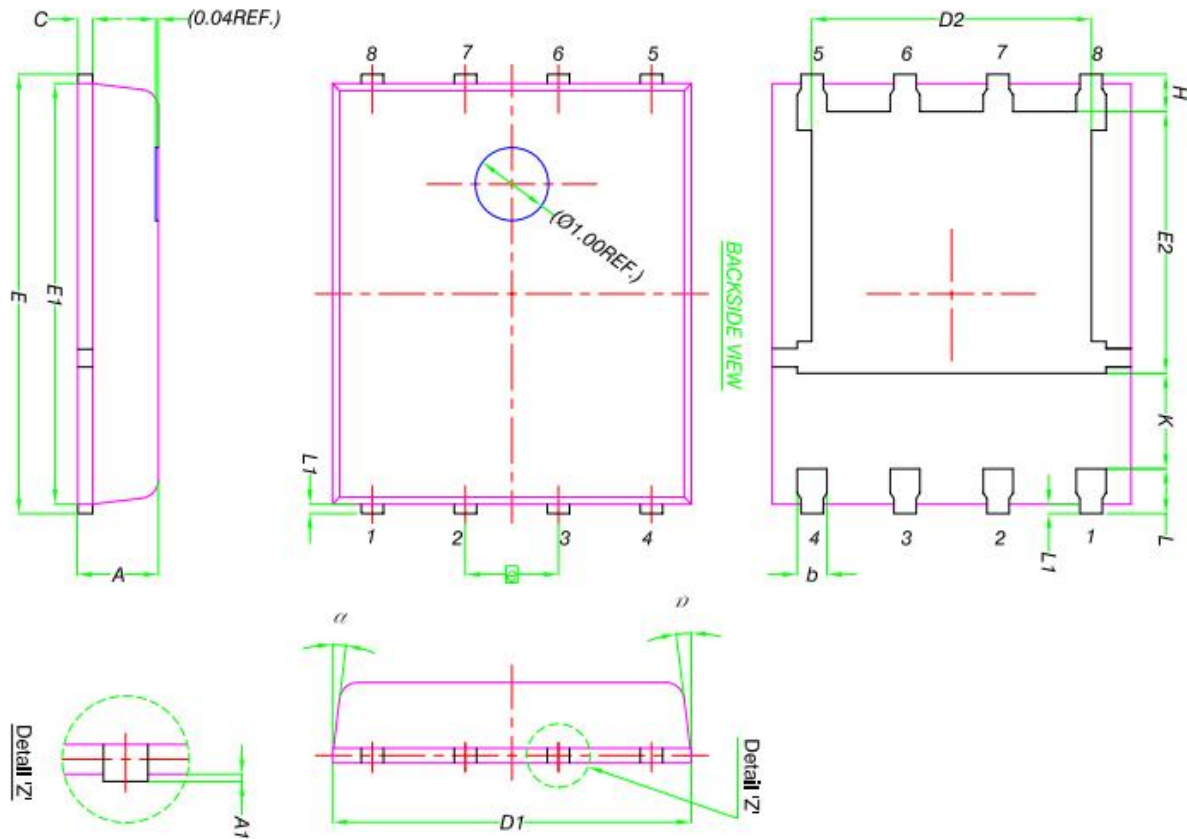


TA-Junction Temperature (°C)  
**Figure 10 Current De-rating**

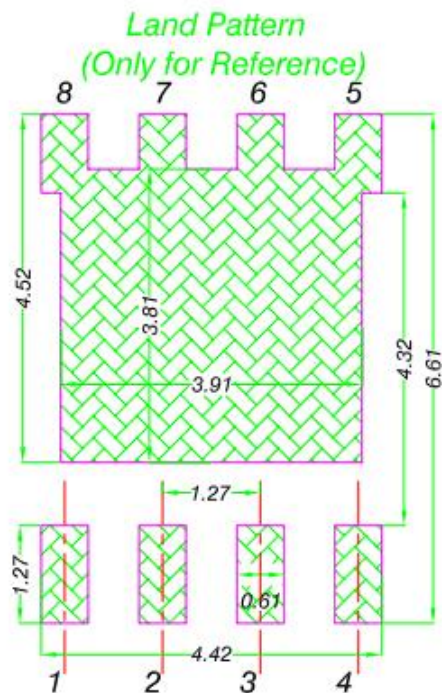


**Figure 11 Normalized Maximum Transient Thermal Impedance**

## DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
$\alpha$	0°	-	12°



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